UMW 1N60

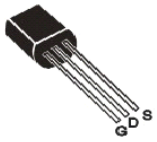
600V N-Channel MOSFET

1.Features

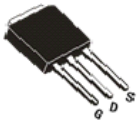
- $V_{DS\ (V)}$=600V
- I_D=1A
- $R_{DS(ON)}$=8.5Ω

2.Pinning Information

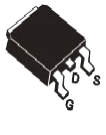
Pin	Symbol	Description
1	G	GATE
2	D	DRAIN
3	S	SOURCE



TO-92



TO-251S



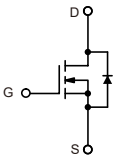
TO-252



TO-251



TO-223



N-Channel

3.Absolute Maximum Ratings T_C= 25°C

Parameter		Symbol	Rating	Units
Drain-source Voltage		V_{DS}	600	V
gate-source Voltage		V_{GS}	±30	V
Continuous Drain Current	T_C=25°C	I_D	1*	A
Continuous Drain Current	T_C=100°C	I_D	0.6*	A
Drain Current - Pulsed ①		I_{DM}	4*	A
Power Dissipation (T_A=25°C)	TO-92	P_D	12.5	W
	TO-223		8	W
	TO-251/251S/252		27	W
Junction Temperature		T_J	150	°C
Storage Temperature		T_{STG}	-55 to 150	°C
Single Pulse Avalanche Energy ②		E_{AS}	14	mJ

Notes: *Drain current limited by maximum junction temperature

4.Thermal resistance rating

Parameter	Symbol	Max		Units
		TO-92	TO-251T/251S/252/223	
Thermal Resistance Junction-lead	R_{thJL}	41.67	4.46	°C/W
Thermal Resistance Junction-ambient	R_{thJA}	140	110	°C/W

5.Electrical Characteristic (T_C=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Drain-source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	600			V
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{DSS}}{\Delta T_J}$	I_D=250μA Referenced to 25°C		0.6		V/°C
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2		4	V
Drain-source Leakage Current	I_{DSS}	V_{DS}=600V, V_{GS}=0V, T_J=25°C			1	μA
		V_{DS}=480V, V_{GS}=0V, T_J=125°C			10	μA
Forward Transconductance	g_{fs}	V_{DS}=40V, I_D=0.5A ③	0.5			S
Gate-body Leakage Current (V_{DS}=0)	I_{GSS}	V_{GS}=±30V			±100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=0.5A ③		8.5	11	Ω
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz		150		pF
Output capacitance	C_{oss}			25		pF
Reverse transfer capacitance	C_{rss}			5.4		pF
Turn -Off Delay Time	$t_{D(off)}$	V_{DD}=300V, I_D=1A, R_G=25Ω ③		13		ns
Total Gate Charge	Q_g	I_D=1A, V_{DS}=480V, V_{GS}=10V ③		4.8		nC
Gate-to-Source Charge	Q_{gs}			0.7		nC
Gate-to-Drain Charge	Q_{gd}			2.7		nC
Continuous Diode Forward Current	I_S				1	A
Diode Forward Voltage	V_{SD}	T_J=25°C, I_S=0.5A, V_{GS}=0V ③			1.4	V
Reverse Recovery Time	t_{rr}	T_J=25°C, I_F=1A di/dt=100A/μs ③		190		ns
Reverse Recovery Charge	Q_{rr}			0.53		nC

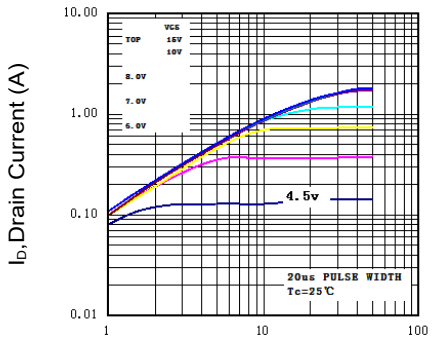
Notes:

① Repetitive rating: Pulse width limited by maximum junction temperature.

② T_J=25°C, V_{DD}=50V, L=30mH, R_G=25Ω, I_{AS}=1.0A, Starting T_J=25°C, V_{DD} =50V, L=30mH, R_G =25Ω, I_{AS}=1A.

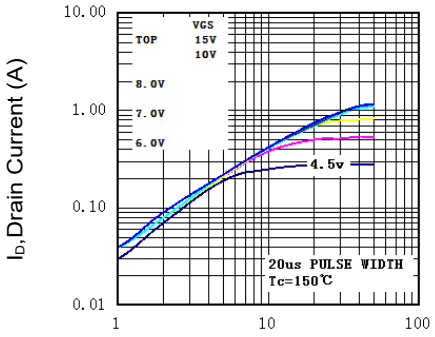
③ Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.

6.Typical Characteristic



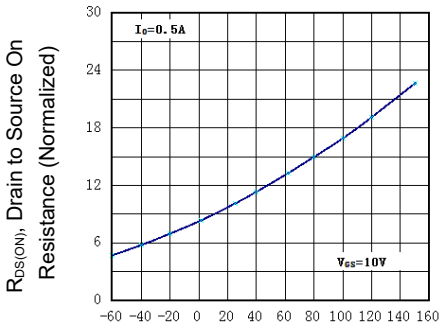
V_{DS},Drain to Source Voltage (V)

Figure 1: Typical Output Characteristics, Tc=25°C



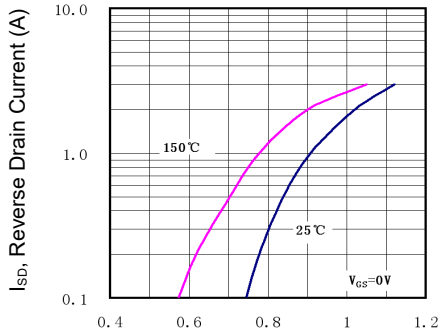
V_{DS},Drain to Source Voltage (V)

Figure 2: Typical Output Characteristics, Tc=150°C



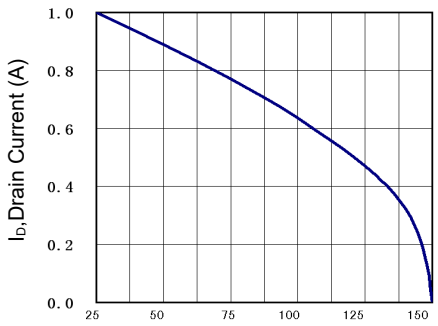
T_J,Junction Temperature (°C)

Figure 3: Normalized On-Resistance Vs.Temperature



V_{SD},Source to Drain Voltage (V)

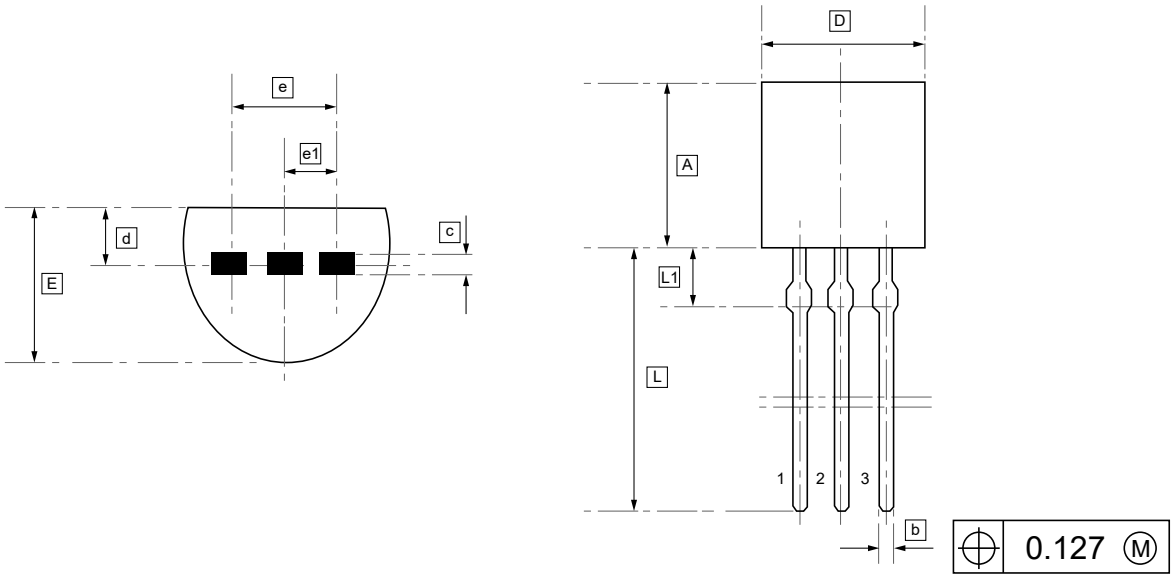
Figure 4: Typical Source-Drain Diode Forward Voltage



T_C,Case Temperature (°C)

Figure 5: Maximum Drain Current Vs.Case Temperature

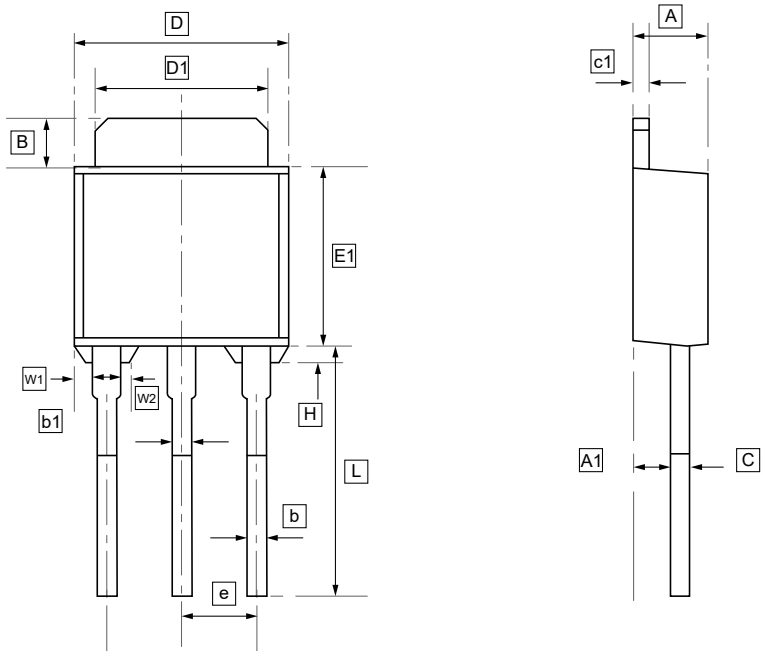
7.1 TO-92 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	b	c	D	d	E	e	e1	L	L1
Min	4.30	0.30	0.30	4.30	1.00	3.20	2.54	1.27	12.70	1.50
Max	5.30	0.55	0.50	5.20	1.70	4.20			15.00	2.00

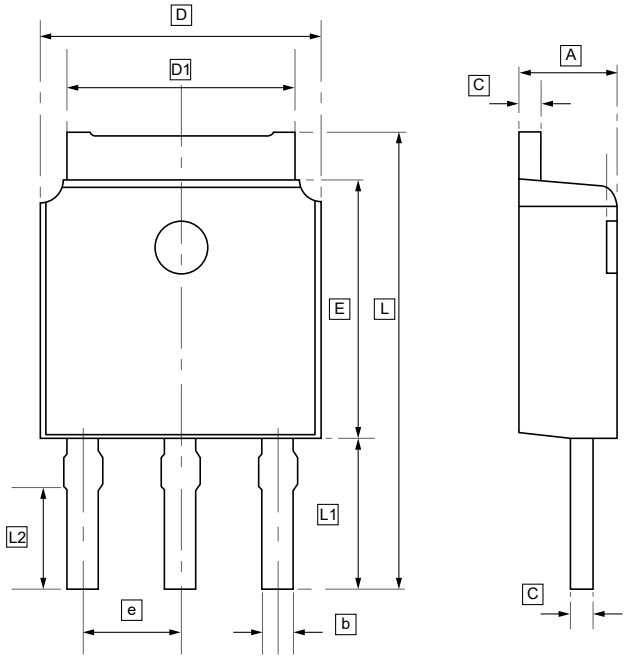
7.2 TO-251T (IPAK) Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	B	b	b1	c	c1	D	D1	E	e	L	H	W1	W2
Min	2.10	0.95	0.80	0.50	0.70	0.45	0.45	6.35	5.10	5.30	2.25	7.00	0.35	0.30	0.20
Max	2.50	1.30	1.25	0.80	0.80	0.70	0.70	6.80	5.50	6.30	2.35	9.20	0.45	0.50	0.40

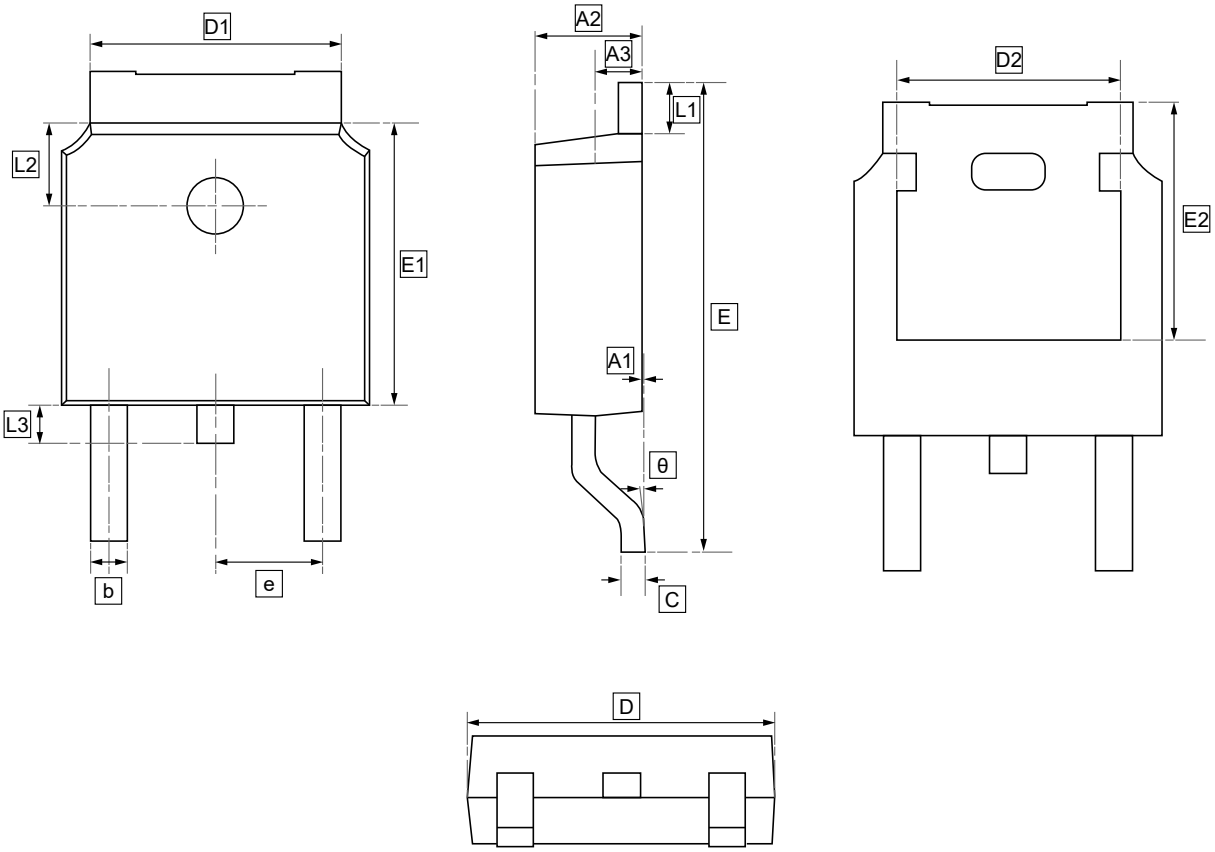
7.3 TO-251S Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	b	C	D	D1	E	e	L	L1	L2
Min	2.20	0.60	0.45	6.50	5.10	5.9	2.18	11.00	4.8	3.5
Max	2.40	0.85	0.60	6.70	5.50	6.20	2.38	12.40	5.3	4.2

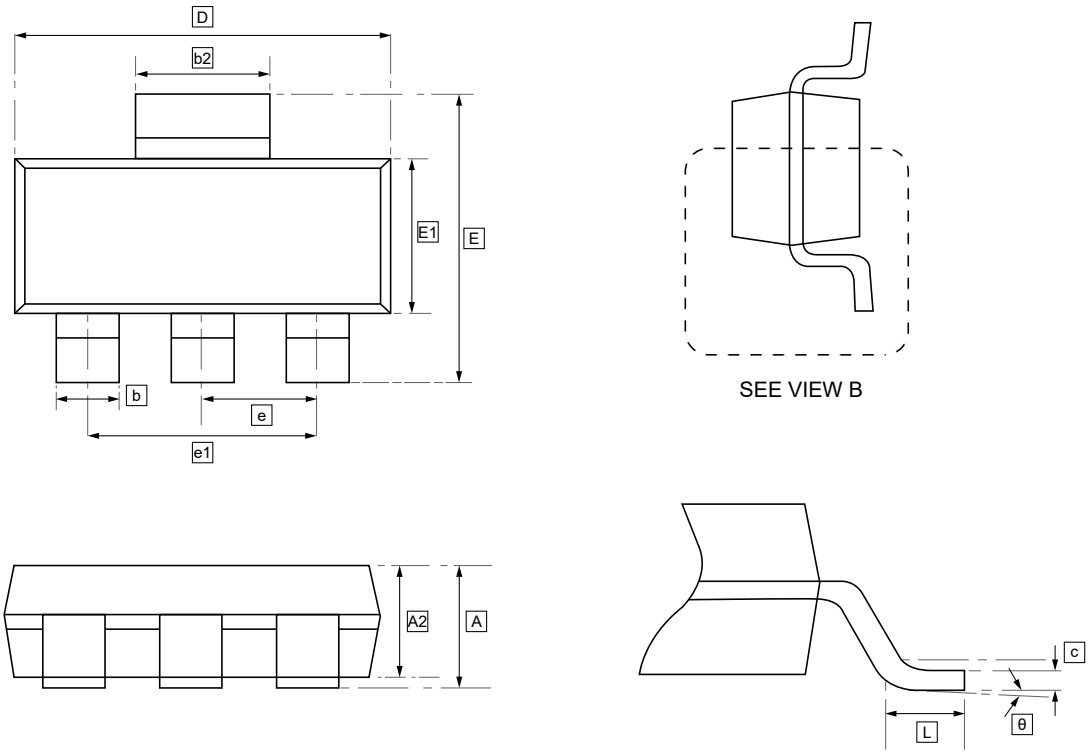
7.4 TO-252 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A1	A2	A3	b	c	D	D1	D2	E	E1	E2	e	L1	L2	L3	θ
Min	0.00	2.18	0.90	0.65	0.46	6.35	4.95	4.32	9.40	5.97	5.21	2.286	0.89	1.70	0.60	0.00
Max	0.13	2.39	1.10	0.85	0.61	6.73	5.46	4.90	10.41	6.22	5.38	BSC	1.27	1.90	1.00	8.00

7.5 SOT-223 Package Outlie Dimensions

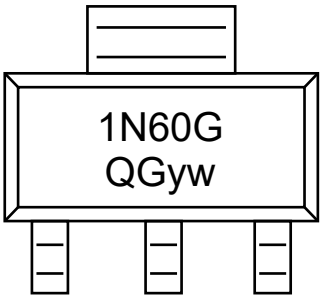


DIMENSIONS (mm are the original dimensions)

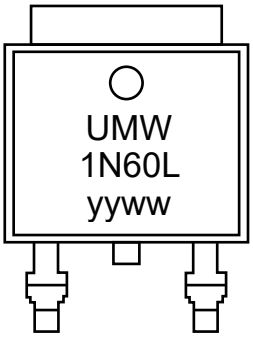
Symbol	A	A1	A2	b	b2	c	D	E	E1	e	e1	L	θ
Min	1.50	0.02	1.50	0.66	2.90	0.23	6.30	6.70	3.30	2.30	4.60	0.90	0°
Max	1.80	0.10	1.70	0.84	3.10	0.33	6.70	7.30	3.70	BSC	BSC	1.10	8°

8.Ordering Information

SOT-223



TO-252



yy: Year Code
ww: Week Code

Order Code	Marking code	Package	Base QTY	Delivery Mode
UMW 1N60G	1N60G	SOT-223	2500	Tape and reel
UMW 1N60L	1N60L	TO-252	2500	Tape and reel

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